

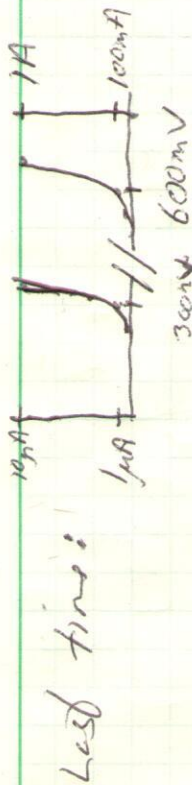
HW2

piazza, sources, web page  
ask!

Diodes

BJTs

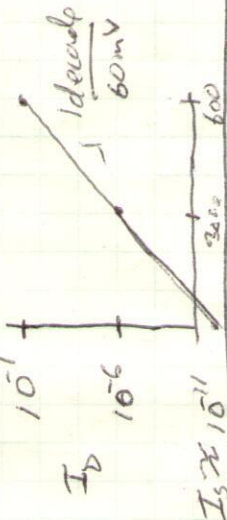
FETs



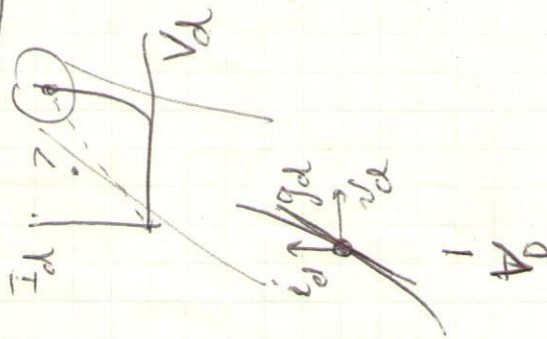
exactly same shape  
 $V_D/V_{TH}$

$$I_D \approx I_S e$$

$$I_D \approx I_S \left( \frac{V_D}{V_{TH}} \right)^2$$



explains resistive effects



$$r_d = \frac{1}{g_d}$$

$$g_d = \frac{\partial I_D}{\partial V_D} = \frac{I_D}{V_{TH}}$$

$$r_d = \frac{V_{TH}}{I_D}$$

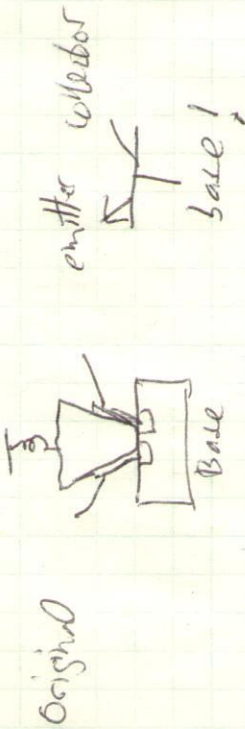
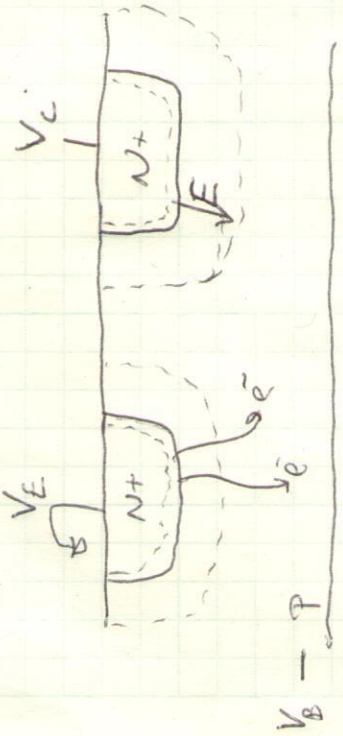
Linearization  

 What's the bias point?  
 Voltage?  
 current?  
 What's the small signal model?

$$v = \left\{ \text{large signal bias} \right\} + \left\{ r_d \right\} = I_D(V_D)$$

SS model

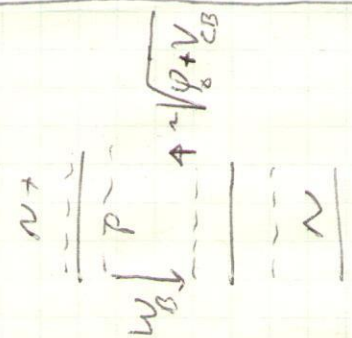
$I_D, V_D$



Current flow to emitter depends on gradient

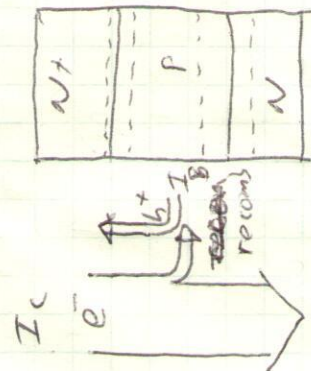
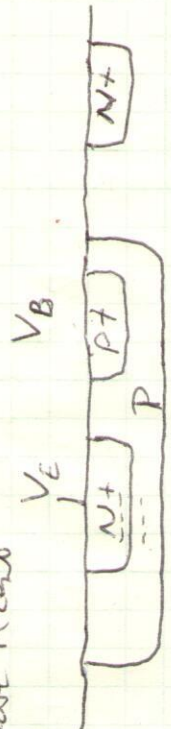
$$J_n = q D_n \frac{dn_p}{dx} = q D_n \frac{n_{p0} e^{V_D/V_{TH}}}{W_B}$$

$W_B$  depends on  $V_{CB}$



~~Handwritten scribble~~

More rec'd



exponential in  $V_D/V_{TH}$   
 $\approx 0$  at edge of depl. region

$$I_C = \beta I_B$$

$$\beta = 10 - 400$$

$$I_C = I_S e^{V_{BE}/V_{TH}} \left( 1 + \frac{V_{CE}}{V_A} \right)$$

$$g_m = \frac{\partial I_C}{\partial V_{BE}} = \frac{I_C}{V_{TH}}$$

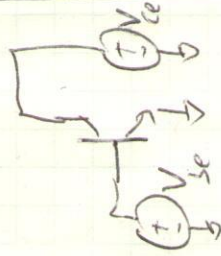
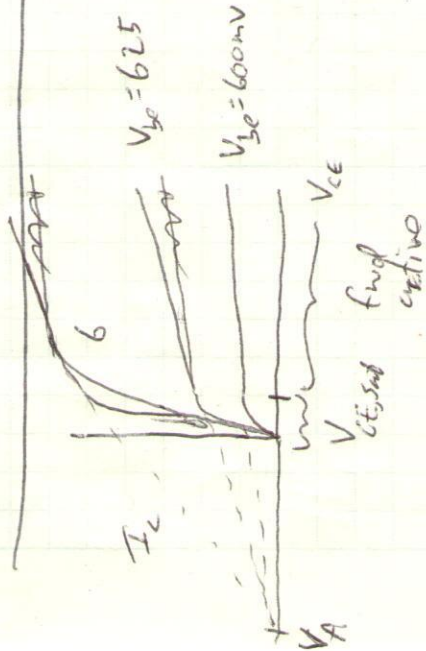
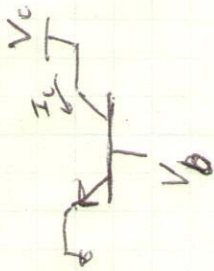
$$g_0 = \frac{\partial I_C}{\partial V_{CE}} = \frac{I_C}{V_A}$$

$$r_T = \left( \frac{\partial I_C}{\partial V_{SE}} \right)^{-1} = \left( \frac{1}{\beta} g_m \right)^{-1}$$





create an ehp - where does it go?



Intrinsic gain

$$A_v = \frac{g_m}{g_o} = g_{m0} = \frac{I_c}{V_{TH}} = \frac{V_A}{V_{TH}} = \frac{I_c}{I_c} = 1$$

10-100V ←  $V_A$   
25mV ←  $V_{TH}$

$$= 400 - 4,000!$$